

## ABSTRACT OF THE DISCLOSURE

A solid-state imaging device having a gate structure including an oxide film and a nitride film includes upper layer films (for example, a planarization film, an insulating film, and a protective film) allowing ultraviolet rays having a frequency of 400 nm or less to pass therethrough; and a metal made shield film or an organic film capable of absorbing the ultraviolet rays formed in such a manner as to cover a region of the gate structure (for example, an output gate and a reset gate), excluding a light receiving portion and a transfer portion, of the solid-state imaging device. With this configuration, it is possible to prevent the shift of a threshold voltage  $V_{th}$ , and hence to enhance the reliability of the transfer or reset of electric charges.